

SPECIFICATIONS

The HCS L36 Advanced System permits the characterization of metallic and semiconducting samples according to the well-known 4-point measurement technique (e.g. Van-der-Pauw, Bar shaped, Greek cross). It measures: electrical resistivity, Hall coefficient, charge carrier concentration and hall mobility.

HCS L36 Advanced

Input current:	DC ~ 1 nA up to 120 mA / AC ~ 16 μ A up to 20 mA
Input impedance:	> 100 G Ω
Compliance voltage:	+/- 12 V
Hall tension:	DC 1 μ V up to 2.5V / AC 20 nV up to 1 V
Max. digital resolution:	300 pV
Carrier concentration:	$10^7 \sim 10^{22}$ cm ³
Resistivity:	$10^{-5} \sim 10^7$ Ω ·cm
Mobility:	$1 \sim 10^7$ cm ² V ⁻¹ s ⁻¹
Sample geometry:	Board for samples smaller than 12.5mm x 12.5mm From thin films up to bulk samples with 2mm in height
Magnetic field.	Hallbach magnet with 0.5T (inner diameter 40mm)
Sensors:	RT up to 600°C